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FDS6294

30V N-Channel Fast Switching PowerTrench® MOSFET

General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

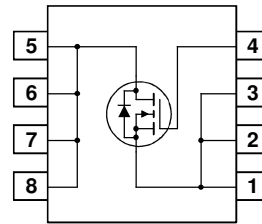
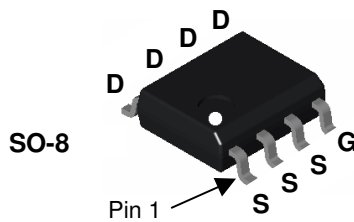
Applications

- DC/DC converter
- Power management
- Load switch



Features

- 13 A, 30 V. $R_{DS(ON)} = 11.3 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$
 $R_{DS(ON)} = 14.4 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- Low gate charge (10 nC typical)
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability.
- RoHS Compliant



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous (Note 1a)	13	A
	– Pulsed	50	
P_D	Power Dissipation for Single Operation (Note 1a)	3.0	W
	(Note 1b)	1.2	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	181	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to $+175$	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1b)	125	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6294	FDS6294	13"	12mm	2500 units

Electrical Characteristics

T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV _{DSS}	Drain–Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		27		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μA
I _{GSS}	Gate–Body Leakage	V _{GS} = ± 20 V, V _{DS} = 0 V			±100	nA

On Characteristics (Note 2)

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	1	1.8	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		–5		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	V _{GS} = 10 V, I _D = 13 A V _{GS} = 4.5 V, I _D = 12 A V _{GS} = 10 V, I _D = 13 A, T _J = 125°C		9.4 11.5 13.5	11.3 14.4 16.5	mΩ
I _{D(on)}	On–State Drain Current	V _{GS} = 10 V, V _{DS} = 5 V	50			A
g _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 13 A		48		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 15 V, V _{GS} = 0 V, f = 1.0 MHz		1205		pF
C _{oss}	Output Capacitance			323		pF
C _{rss}	Reverse Transfer Capacitance			102		pF
R _G	Gate Resistance		V _{GS} = 15 mV, f = 1.0 MHz		0.9	

Switching Characteristics (Note 2)

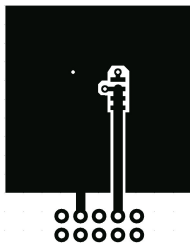
t _{d(on)}	Turn–On Delay Time	V _{DD} = 15 V, I _D = 1 A, V _{GS} = 10 V, R _{GEN} = 6 Ω		9	18	ns
t _r	Turn–On Rise Time			4	8	ns
t _{d(off)}	Turn–Off Delay Time			24	48	ns
t _f	Turn–Off Fall Time			6	12	ns
Q _g	Total Gate Charge	V _{DS} = 15 V, I _D = 13 A, V _{GS} = 5 V		10	14	nC
Q _{gs}	Gate–Source Charge			3.5		nC
Q _{gd}	Gate–Drain Charge			3		nC

Drain–Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain–Source Diode Forward Current			2.1		A
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.1 A (Note 2)		0.74	1.2	V
t _{rr}	Diode Reverse Recovery Time	I _F = 13 A, dI _F /dt = 100 A/μs		25		ns
Q _{rr}	Diode Reverse Recovery Charge			14		nC

Notes:

- R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design.



a) 50 °C/W when mounted on a 1 in² pad of 2 oz copper



b) 125 °C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

- Test: Pulse Width < 300 μs, Duty Cycle < 2.0%
- Starting T_J = 25 °C, L = 3 mH, I_{AS} = 11 A, V_{DD} = 30 V, V_{GS} = 10 V

Typical Characteristics

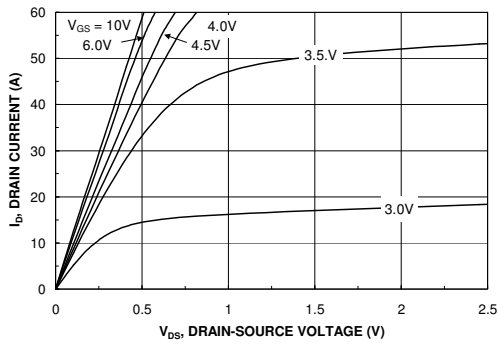


Figure 1. On-Region Characteristics.

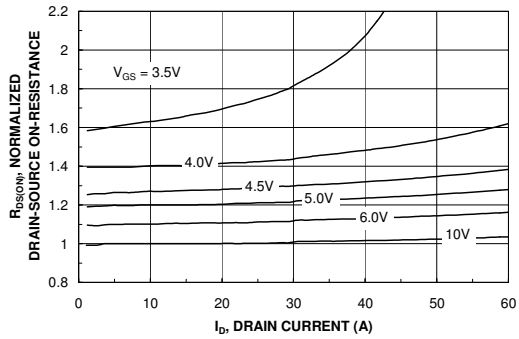


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

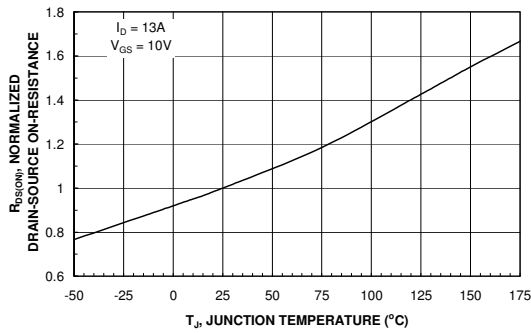


Figure 3. On-Resistance Variation with Temperature.

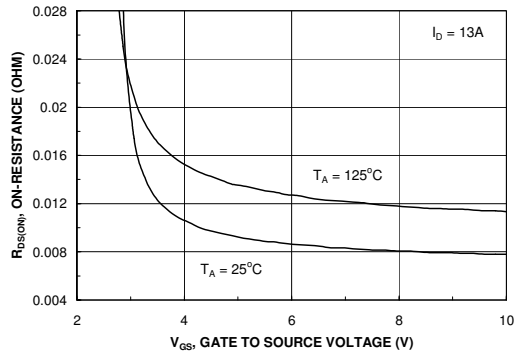


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

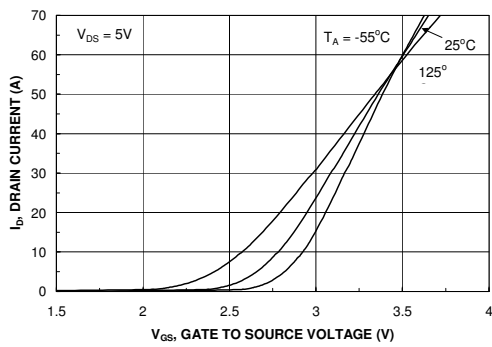


Figure 5. Transfer Characteristics.

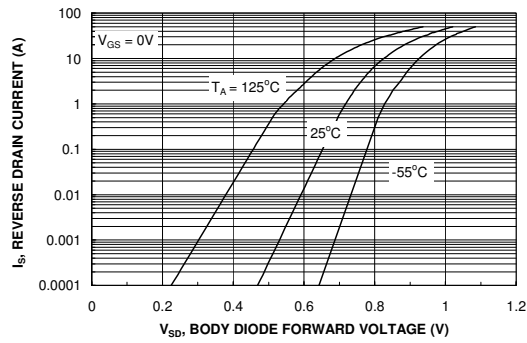


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

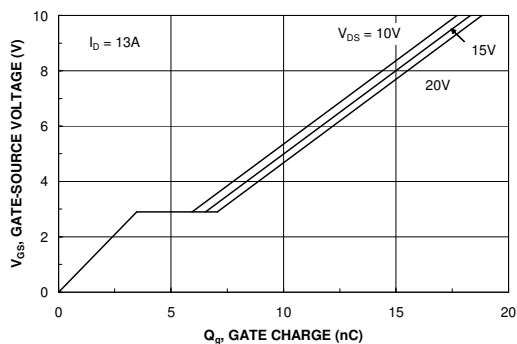


Figure 7. Gate Charge Characteristics.

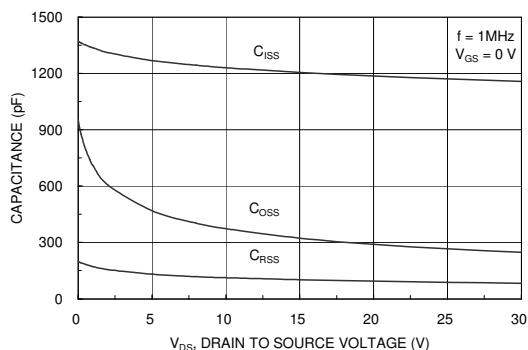


Figure 8. Capacitance Characteristics.

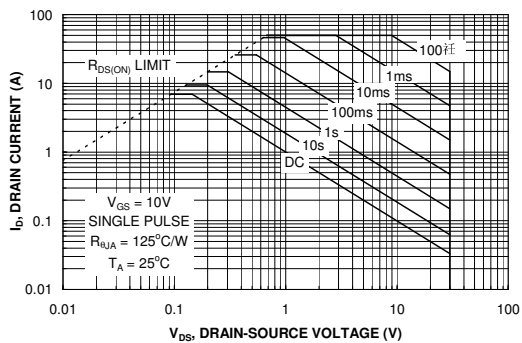


Figure 9. Maximum Safe Operating Area.

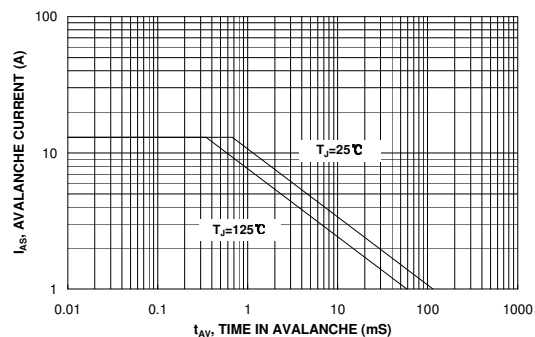
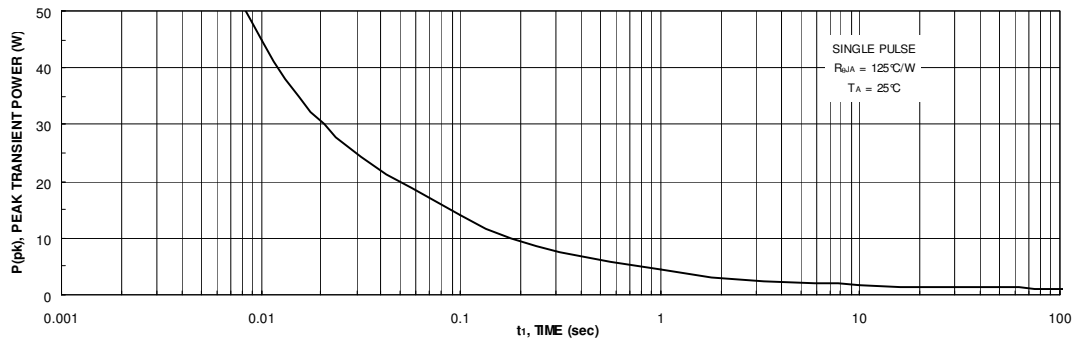


Figure 10. Unclamped Inductive Switching Capability Figure



11. Single Pulse Maximum Power Dissipation.

Typical Characteristics

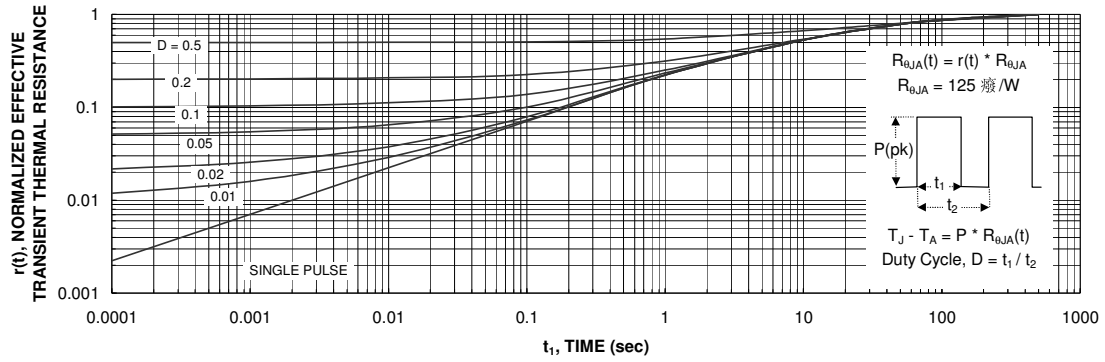


Figure 12. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
 Transient thermal response will change depending on the circuit board design.

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